

WST2004

N-Ch MOSFET

General Description

The WST2004 is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent R_{DSON} and gate charge for most of the small power switching and load switch applications.

The WST2004 meet the RoHS and Green Product requirement with full function reliability approved.

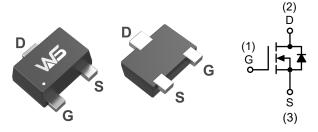
Product Summery

BV _{DSS}		I _D
20V	240mΩ	0.6A

Applications

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

SOT-723-3L Pin Configuration



Features

- Lead Free Product is Acquired
- Surface Mount Package
- N-Channel Switch with Low R_{DS}(on)
- Operated at Low Logic Level Gate Drive

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	± 8	V
I _D @T _A =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	600	mA
I _{DM}	Pulsed Drain Current ²	1.2	А
P _D @T _A =25℃	Total Power Dissipation ³	0.150	W
R _{θJA}	Thermal Resistance from Junction to Ambient (note 1)	823	°C/W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
TL	Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	260	°C



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Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	20			V	
$\triangle BV_{DSS} / \triangle T_J$	BV _{DSS} Temperature Coefficient	Reference to 25 $^\circ\!\!{\rm C}$, I_D=1mA		0.05		V/℃	
		V _{GS} =4.5V , I _D =0.4A	240 450				
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =2.5V , I _D =0.3A		280	765	mΩ	
· (00)		V _{GS} =1.8V , I _D =0.2A		410	850	mΩ	
		V _{GS} =1.5V , I _D =0.1A		450	950		
V _{GS(th)}	Gate Threshold Voltage		0.35	0.6	1.0	V	
	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, I _D =250uA		-3.7		mV/℃	
	Drain-Source Leakage Current	V _{DS} =16V , V _{GS} =0V , T _J =25℃			1		
I _{DSS}		V _{DS} =16V , V _{GS} =0V , T _J =55℃			5	- uA	
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 8V$, $V_{DS}=0V$			±10	uA	
gfs	Forward Transconductance	V _{DS} =5V , I _D =0.1A		1.5		S	
T _{d(on)}	Turn-On Delay Time			2.9			
Tr	Rise Time	V _{DD} =15V , V _{GS} =10V ,		5.8			
T _{d(off)}	Turn-Off Delay Time	R _G =6Ω, I _D =0.1A		9		ns	
T _f	Fall Time			18			
C _{iss}	Input Capacitance			88	160		
C _{oss}	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		15	30	pF	
C _{rss}	Reverse Transfer Capacitance			10	22		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,4}				0.1	А
I _{SM}	Pulsed Source Current ^{2,4}	V _G =V _D =0V , Force Current			0.5	А
V _{SD}	Diode Forward Voltage ²	$V_{GS}\text{=}0V$, $I_{S}\text{=}0.2A$, $T_{J}\text{=}25^{\circ}\!\mathrm{C}$			1.2	V

Notes :

1, Surface mounted on FR4 board using the minimum recommended pad size.

2. Pulse Test : Pulse Width=300µs, Duty Cycle=2%.

3. Switching characteristics are independent of operating junction temperatures.

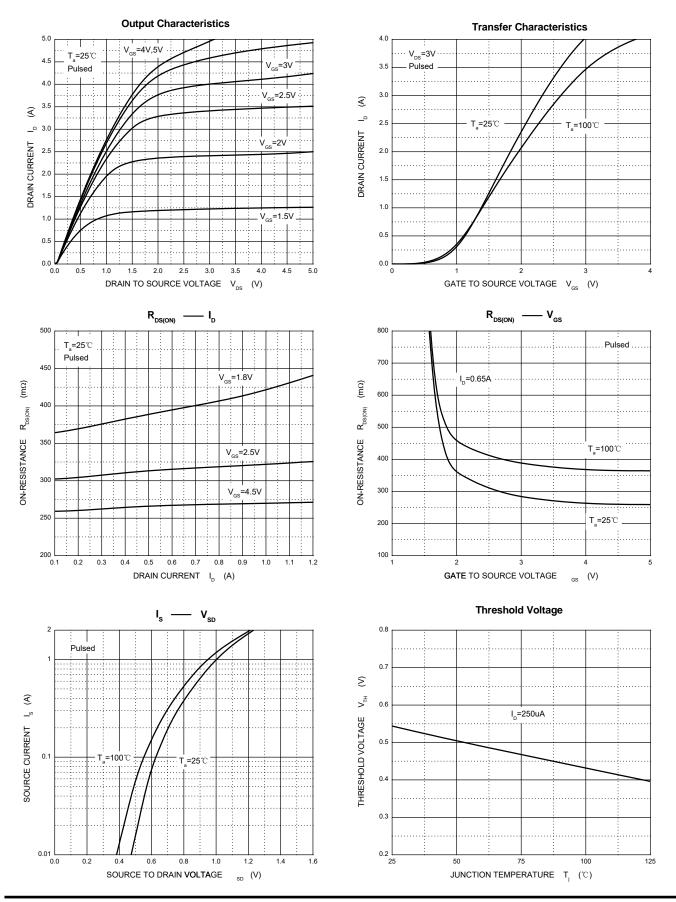
4. Guaranteed by design, not subject to producting.



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Typical Performance Characteristics



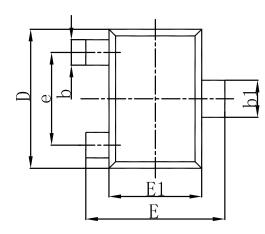
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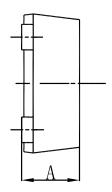


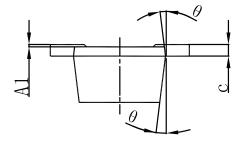
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Packaging information







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	0.430	0.500	0.017	0.020	
A1	0.000	0.050	0.000	0.002	
b	0.170	0.270	0.007	0.011	
b1	0.270	0.370	0.011	0.015	
С	0.080	0.150	0.003	0.006	
D	1.150	1.250	0.045	0.049	
E	1.150	1.250	0.045	0.049	
E1	0.750	0.850	0.030	0.033	
e	0.800	0.800TYP.		0.031TYP.	
θ	7° REF.		7° REF.		



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